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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application No.: 10/803,203 Confirmation No.: 5841
First Named Inventor: Bulucea, Constantin Filing Date: 17 March 2004
Group Art Unit: 2811 Examiner: Unknown
Atty. Docket No.: NS-5737 US
Title: Configuration and Fabrication of Semiconductor Structure Having
N-channel Channel-junction Field-effect Transistor
Assignee(s): National Semiconductor Corporation

Mountain View, California
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INFORMATION DISCLOSURE STATEMENT
UNDER 37 CFR 1.97(b)

Sir:

Pursuant to 37 CFR 1.56, 1.97, and 1.98, each document listed on the accompanying substitute PTO Form 1449 is called to the attention of the Examiner for the above patent application. A copy of each listed document is enclosed.

Nishiuchi et al., Hu et al., and the first-listed Other Art document of Parillo et al. cited here respectively are Nishiuchi et al., Hu et al., and Parillo et al. cited on pages 4 and 5 of the specification of the present application subject to the publication-date information being made more specific for these three documents in the accompanying substitute PTO Form 1449.

Nishida et al. cited here is Nishida et al. cited on page 5 of the specification of the present application subject to the publication-source information being corrected from IRPS Dig. Tech. Paps. as given in the specification to IEDM Tech. Dig. as specified in the accompanying substitute PTO Form 1449. The publication-date information for Nishida et al. has also been made more specific in the substitute PTO Form 1449.

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In contrast to U.S. Patent 6,548,842 B1 in which both the n-channel and p-channel insulated-gate field-effect transistors ("IGFETs") of a complementary-IGFET structure are surface-channel devices, Nakahara et al. proposes a complementary-IGFET structure in which both the n-channel and p-channel IGFETs are channel-junction (buried-channel) devices.

Citation of each listed document shall not be construed as:

1. an admission that the document is necessarily prior art with respect to the instant invention;
2. a representation that a search has been made; or
3. an admission that the information cited herein is, or is considered to be, material to patentability as defined in 37 CFR 1.56(b).

This information disclosure statement is submitted under the provisions of 37 CFR 1.97(b).

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